Amplifier TransistorsNPN Silicon

COLLECTOR

1

2

BASE

3

EMITTER

MAXIMUM RATINGS

Rating	Symbol	BC 546	BC 547	BC 548	Unit
Collector-Emitter Voltage	VCEO	65	45	30	Vdc
Collector - Base Voltage	VCBO	80	50	30	Vdc
Emitter – Base Voltage	VEBO	6.0			Vdc
Collector Current — Continuous	Ic	100			mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 . • 5.0		mW mW/°C	
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12		Watt mW/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150			°C

BC546, B BC547, A, B, C BC548, A, <u>B</u>, C



CASE 29-04, STYLE 17 TO-92 (TO-226AA)

THERMAL CHARACTERISTICS

Characteristic	Symbol	wax	Unit	
Thermal Resistance, Junction to Ambient	R ₀ JA	200	°C/W	
Thermal Resistance, Junction to Case	R ₀ JC	83.3	°C/W	

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage (I _C = 1.0 mA, I _B = 0)	BC546 BC547 BC548	V(BR)CEO	65 45 30	_ _ _		V	
Collector – Base Breakdown Voltage (I _C = 100 μAdc)	BC546 BC547 BC548	V(BR)CBO	80 . 50 30	_ _ _		٧	
Emitter-Base Breakdown Voltage (IE = 10 μA, IC = 0)	BC546 BC547 BC548	V(BR)EBO	6.0 6.0 6.0	_ _ _	_ _ _	V	
Collector Cutoff Current (VCE = 70 V, VBE = 0) (VCE = 50 V, VBE = 0) (VCE = 35 V, VBE = 0) (VCE = 30 V, TA = 125°C)	BC546 BC547 BC548 BC546/547/548	ICES		0.2 0.2 0.2 	15 15 15 4.0	. nA μA	



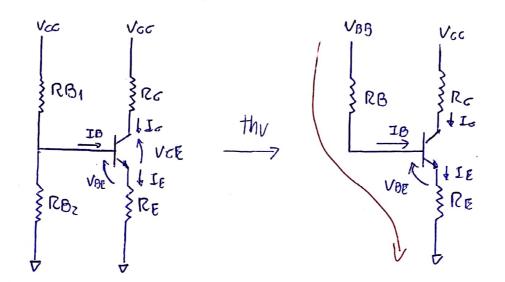
BC546, B BC547, A, B, C BC548, A, B, C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS						
DC Current Gain (IC = 10 μA, VCE = 5.0 V)	BC547A/548A BC546B/547B/548B BC548C	hFE	- - -	90 150 270	• - - -	_
(IC = 2.0 mA, V _{CE} = 5.0 V)	BC546 BC547 BC548 BC547A/548A BC546B/547E/548B BC547C/BC548C		110 110 110 110 110 1200 420	180 290 520	450 800 800 220 450 800	
(I _C = 100 mA, V _{CE} = 5.0 V)	BC547A/548A BC546B/547B/ <mark>548B</mark> BC548C		_ 	120 180 300		
Collector – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA) (I _C = 10 mA, I _B = See Note 1)		VCE(sat)	_ _ _	0.09 0.2 0.3	0.25 0.6 0.6	V
Base – Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA)		VBE(sat)		0.7	الحيد د	. V
Base-Emitter On Voltage (IC = 2.0 mÅ, V _{CE} = 5.0 V) (IC = 10 mA, V _{CE} = 5.0 V)		VBE(on)	0.55		0.7	V
SMALL-SIGNAL CHARACTERISTICS			` ` ` ` ` ` ` ` ` ` ` ` ` ` ` ` ` ` ` `			
Current – Gain — Bandwidth Product (IC = 10 mA, VCE = 5.0 V, f = 100 MHz)	BC546 BC547 BC548	fΤ	150 150 150	300 300 300	_ _ _	MHz
Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)		C _{obo}	_	1.7	4.5	pF
Input Capacitance (VEB = 0.5 V, IC = 0, f = 1.0 MHz)		C _{ibo}		10	_	pF
Small–Signal Current Gain (I _C = 2.0 mA, V _{CE} = 5.0 V, f = 1.0 kHz)	BC546 BC547/548 BC547A/548A BC546B/547B/548B BC547C/548C	h _{fe}	125 125 125 240 450	220 330 600	500 900 260 500 900	-
Noise Figure (I _C = 0.2 mA, \dot{V}_{CE} = 5.0 V, R _S = 2 k Ω , f = 1.0 kHz, Δf = 200 Hz)	BC546 BC547 BC548	NF		2.0 2.0 2.0	10 10 • 10	dB

Note 1: I_B is value for which I_C = 11 mA at V_{CE} = 1.0 V.

BC548B NJBJ



$$VBB - VBE = IB \left(\frac{1+\beta}{2\beta} RE + RB \right)$$

$$VBB-VBE = IBB(RE + RB)$$
 I_{σ}

$$\frac{VBB-VBE}{RE+RB}=I_{c}$$

$$V_{BB} = I_{c} \left(\frac{RB}{\beta} + RE \right) + V_{BE}$$

Ly LA ne cesito en señal pero Aumentar rib pero Afecta ganana = 7 Utilizo la mas Chica

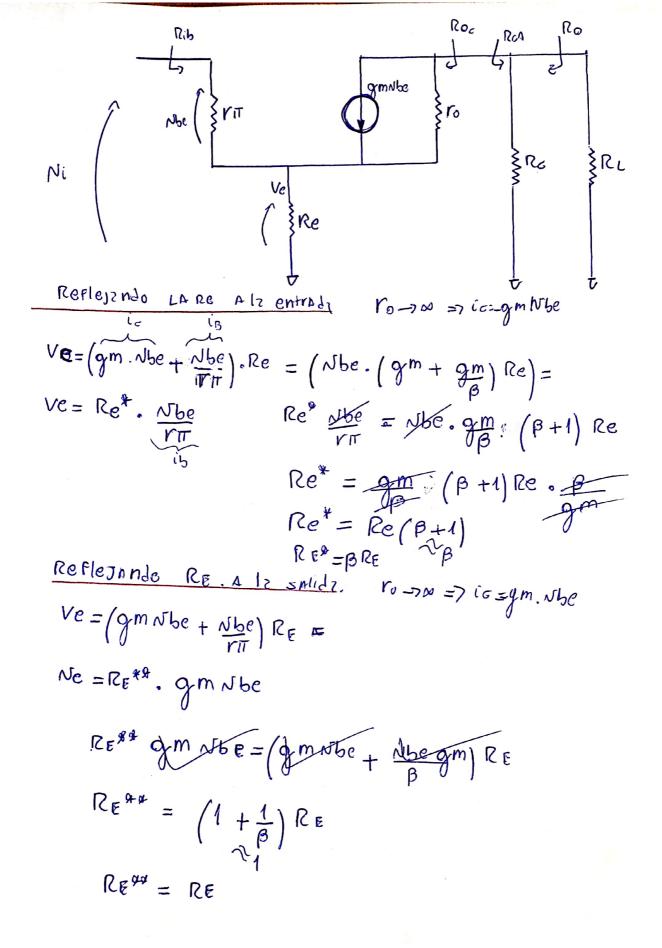
$$V_{CC} = V_{BB} \cdot \left(\frac{RB_2 + RB_1}{RB_2}\right) = 42V$$

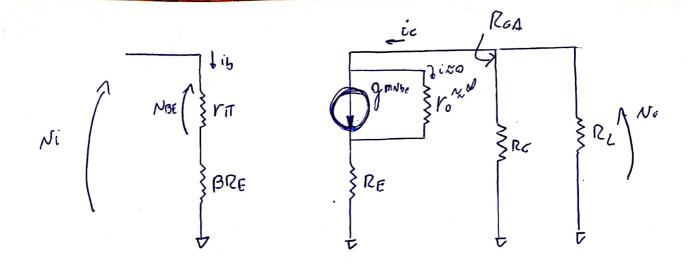
$$VBB = 6V. \frac{100K}{87K + 100K} = 3,3V$$

$$Vcc = 9V$$

$$gm = \frac{Ica}{Vth} = 16Zm$$

$$I_c = 7m$$





$$Av = -\frac{B}{BRE + B}$$
 $RCA = -\frac{RCA}{RE + \frac{1}{gm}}$

$$Av = -1,9$$

$$Av = -1,91$$